

High Power Laser Diode Chip



Part Number: CHP-105

High Power Chip
Multi-Mode Fabry-Perot
CW Wavelength at 1450nm



Features

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard Bare Die
- Cost Effective

Application

- Professional Medical



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

High Power Laser Diode Chip



Specification

CHP-105



| Optical | Symbol | Typ. | Units |
|-----------------------|----------------------|-----------|----------------------|
| Center Wavelength | λ_c | 1450 | nm (± 20) |
| Output Power (CW)* | P_{out} | 5 | watts ($\pm 10\%$) |
| Chip Cavity Length | CL | 2500 | μm |
| Emitter Width | W | 95 | μm |
| Spectral Width FWHM | $\Delta\lambda$ | 15 | nm |
| Slope Efficiency | η | 0.4 | W/A |
| Fast Axis Div. | θ_{\perp} | 28 | deg FWHM |
| Slow Axis Div. | θ_{\parallel} | 9 | deg FWHM |
| Electrical | Symbol | | Units |
| Power Conversion Eff. | η | 21 | % |
| Threshold Current | I_{TH} | 0.5 | A |
| Operating Current | I_{op} | 14 | A |
| Operating Voltage | V_{op} | 1.7 | V |
| Mechanical | | Range | Units |
| Operating Temp.** | | -40 to 60 | $^{\circ}\text{C}$ |
| Storage Temp. | | -40 to 80 | $^{\circ}\text{C}$ |

*Specified values are rated at a constant heat sink temperature of 20°C.

**High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.

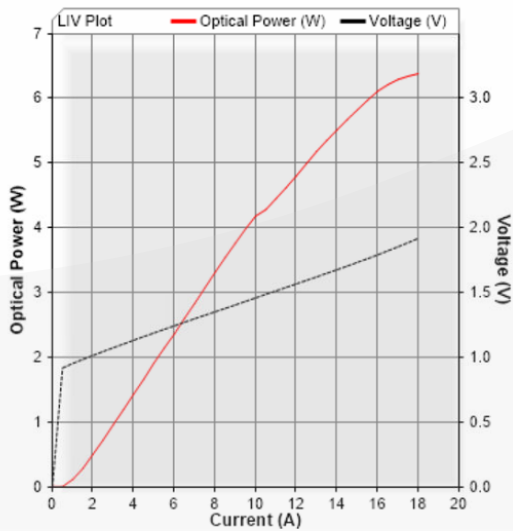
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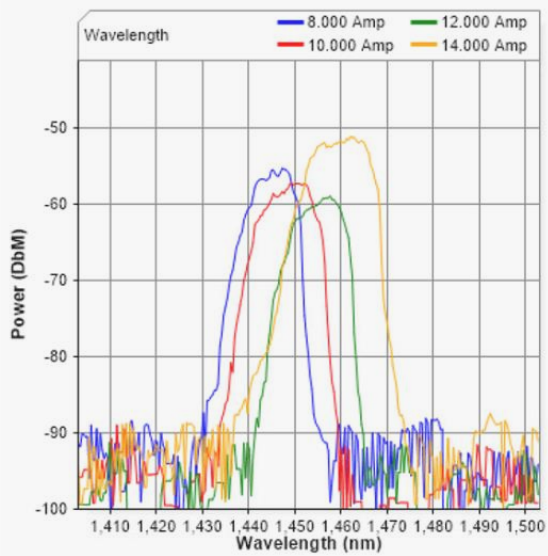
SemiNex Laser Diodes CHP-105

Graphs & Data

Typical CHP L-I-V Characteristics



Typical CHP Output Spectrum

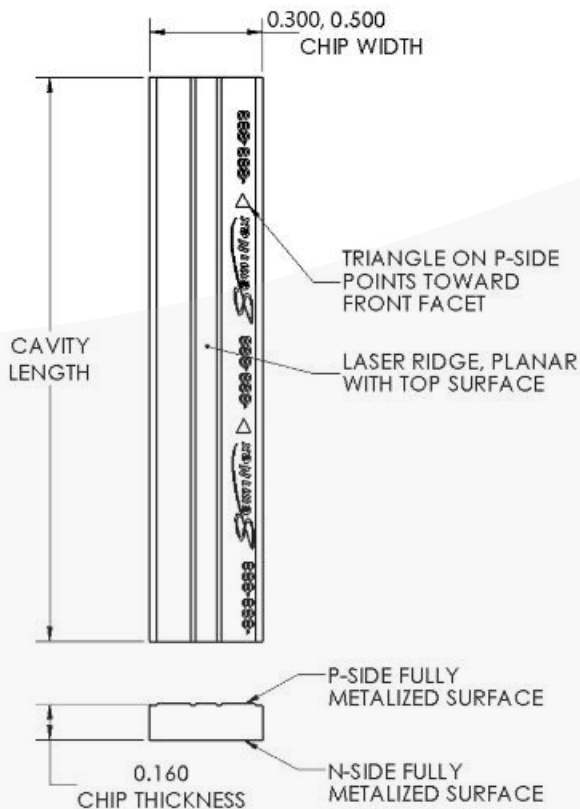


*Graphs and Data were collected from mounted parts

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Mechanical Drawing



CHIP ATTRIBUTES

| | |
|----------------------------------|---|
| APERTURE WIDTH (μm) | Single Mode (4, 5) ± 1 Multi Mode (50, 95, 180, 350) ± 3 |
| CHIP WIDTH (μm) | 300, 500 ± 10 |
| THICKNESS (μm) | 160 ± 10 |
| CAVITY LENGTH (μm) | Varies ± 10 |

P METALIZATION

| MATERIAL | THICKNESS (nm) | TOLERANCE (nm) |
|----------|----------------|----------------|
| Ti | 50 | ± 10 |
| Pt | 125 | ± 25 |
| Au | 250 | ± 50 |

N METALIZATION

| MATERIAL | THICKNESS (nm) | TOLERANCE (nm) |
|----------|----------------|----------------|
| Ti | 30 | ± 10 |
| Pt | 125 | ± 25 |
| Au | 400 | ± 40 |

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